

<b>Notice of References Cited</b>	Application/Control No. 09/684,904	Applicant(s)/Patent Under Reexamination KON ET AL.
	Examiner THANH V TRAN	Art Unit 2814

**U.S. PATENT DOCUMENTS**

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
A	US-5,874,750	02-1999	Yanagisawa et al.	257	133
B	US-				
C	US-				
D	US-				
E	US-				
F	US-				
G	US-				
H	US-				
I	US-				
J	US-				
K	US-				
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N					
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